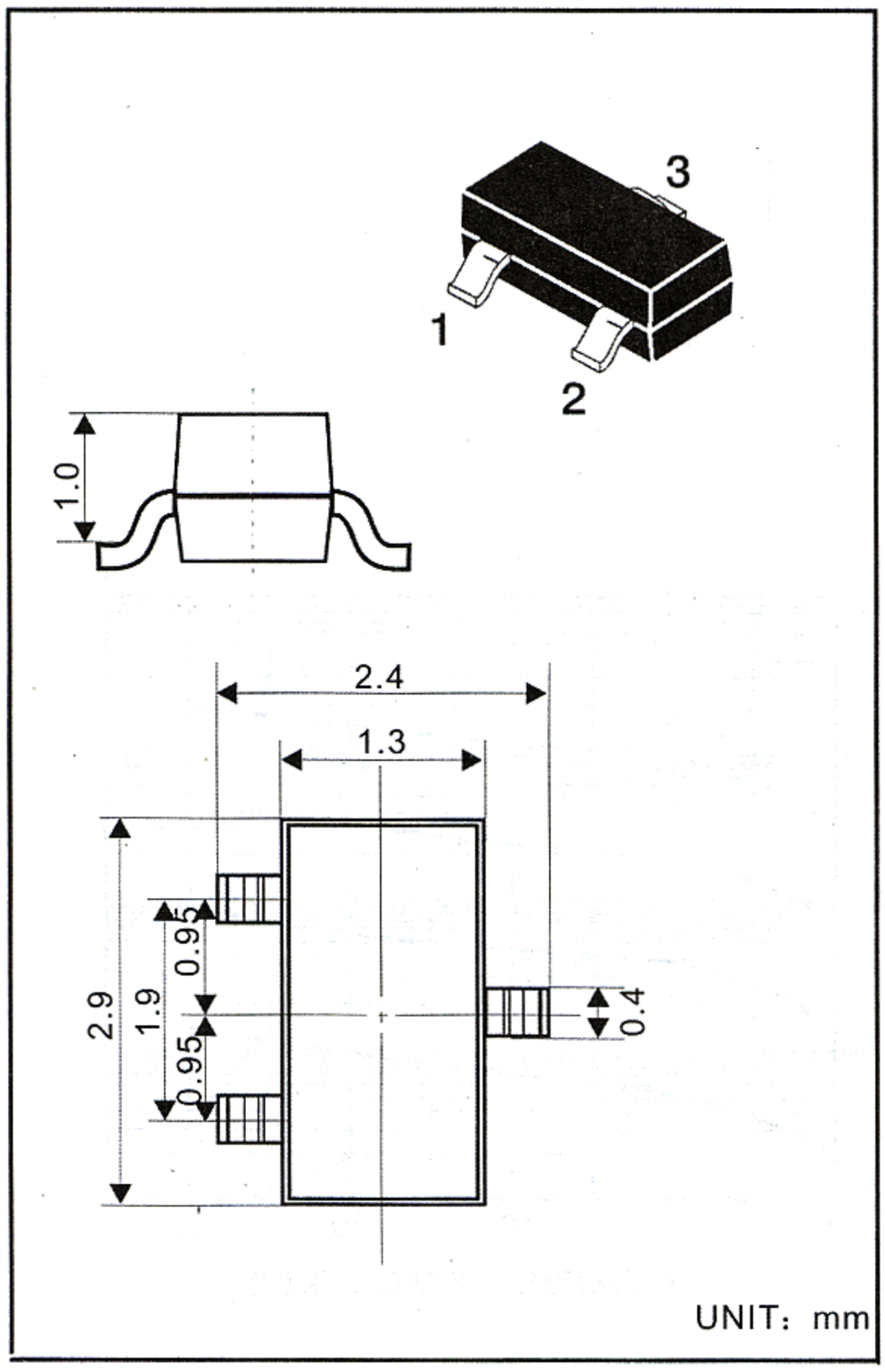
SOT-23 Plastic-Encapsulate DIODES

1SS226 SWITCHING DIODE



FEATURES

Power dissipation

P_D: 150mW (Tamb=25℃)

Forward current

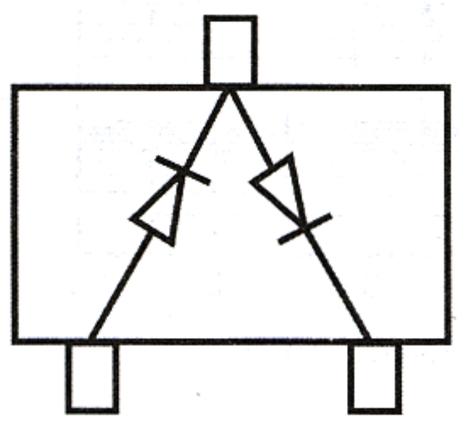
I_F: 100mA

Reverse voltage

V_R: 80V

Operating and storage junction temperature range

T_J, T_{stg} :-55℃ to+150℃



MARKING: C3

ELECTRICAL CHARACTERISTICS

(Tamp=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	I_R=100μA	80		V
Reverse voltage leakage current	I_R	V_R=80V		0.5	μA
Forward voltage	V_F	I_F=100mA		1.2	V
Diode capacitance	C_{tot}	V_R=0V,f=1MHz		3	pF
Reverse recovery time	t_{rr}	I_F=I_R=10mA Irr=0.1I_R		4	ns

Typical Characteristics